Application No.: 10/669,996 Docket No.: 29926/39504

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 1, line 5 with the following amended paragraph:

A method for fabricating a CMOS image sensor is disclosed and, more particularly a method for fabricating a CMOS image sensor is disclosed that reduces the amount of dark current by protecting the surface of a photodiode with spacer etching barrier film during the etching process for formulation of spacers.